

HIGH-SPEED 3.3V 64K x 8 DUAL-PORT STATIC RAM

70V08L

Features

 True Dual-Ported memory cells which allow simultaneous access of the same memory location

High-speed access

- Commercial: 15ns (max.)
- Industrial: 20ns (max.)
- Low-power operation
 - IDT70V08L
 Active: 550mW (typ.)
 - Standby: 1mW (typ.)
- Dual chip enables allow for depth expansion without external logic
- IDT70V08 easily expands data bus width to 16 bits or more using the Master/Slave select when cascading more than one device

- M/S = VIH for BUSY output flag on Master, M/S = VIL for BUSY input on Slave
- Busy and Interrupt Flags
- On-chip port arbitration logic
- Full on-chip hardware support of semaphore signaling between ports
- Fully asynchronous operation from either port
- LVTTL-compatible, single 3.3V (±0.3V) power supply
- Available in a 100-pin TQFP
- Industrial temperature range (-40°C to +85°C) is available for selected speeds
- Green parts available, see ordering information

Functional Block Diagram



NOTES:

1. $\overline{\text{BUSY}}$ is an input as a Slave (M/S-VIL) and an output when it is a Master (M/S-VIH).

BUSY and INT are non-tri-state totem-pole outputs (push-pull).

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70V08L High-Speed 3.3.V 64K x 8 Dual-Port Static RAM

Description

The IDT70V08 is a high-speed 64K x 8 Dual-Port Static RAM. The IDT70V08 is designed to be used as a stand-alone 512K-bit Dual-Port RAM or as a combination MASTER/SLAVE Dual-Port RAM for 16-bitor-more word system. Using the IDT MASTER/SLAVE Dual-Port RAM approach in 16-bit or wider memory system applications results in full-speed, error-free operation without the need for additional discrete logic.

This device provides two independent ports with separate control, address, and I/O pins that permit independent, asynchronous access for reads or writes to any location in memory. An automatic power down feature controlled by the chip enables (either \overline{CE}_0 or CE1) permit the on-chip circuitry of each port to enter a very low standby power mode.

Fabricated using CMOS high-performance technology, these devices typically operate on only 550mW of power.

The IDT70V08 is packaged in a 100-pin Thin Quad Flatpack (TQFP).

Pin Configurations^(1,2,3)



- 1. All Vcc pins must be connected to power supply.
- 2. All GND pins must be connected to ground.
- 3. Package body is approximately 14mm x 14mm x 1.4mm.
- 4. This package code is used to reference the package diagram.

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Industrial and Commercial Temperature Ranges

Absolute Maximum Ratings⁽¹⁾

Symbol	Rating	Commercial & Industrial	Unit
Vterm ⁽²⁾	Terminal Voltage with Respect to GND	-0.5 to +4.6	V
Tbias	Temperature Under Bias	-55 to +125	٥C
Tstg	Storage Temperature	-65 to +150	٥C
Ιουτ	DC Output Current	50	mA

NOTES:

- 1. Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.
- 2. VTERM must not exceed Vcc + 0.3V for more than 25% of the cycle time or 10ns maximum, and is limited to \leq 20mA for the period of VTERM \geq Vcc + 0.3V.

Pin Names

Left Port	Right Port	Names			
CE0L, CE1L	\overline{CE} OR, CE1R	Chip Enables			
R/WL	R/Wr	Read/Write Enable			
ŌĒL	ŌĒr	Output Enable			
Aol - A15l	Aor - A15r	Address			
1/Ool - 1/07l	1/O0r - 1/07r	Data Input/Output			
SEML	SEM R	Semaphore Enable			
ĪNTL	ĪNTr	Interrupt Flag			
BUSYL	BUSYR	Busy Flag			
M	/\$	Master or Slave Select			
V	DD	Power (3.3V)			
V	SS	Ground (0V)			

3740 tbl 04

Maximum Operating Temperature and Supply Voltage⁽¹⁾

Grade	Ambient Temperature	GND	Vdd
Commercial	0°C to +70°C	0V	3.3V <u>+</u> 0.3V
Industrial	-40°C to +85°C	0V	3.3V <u>+</u> 0.3V
			3740 tbl 02

NOTES:

3740 tbl 01

1. This is the parameter TA. This is the "instant on" case temperature.

Capacitance⁽¹⁾ (TA = $+25^{\circ}$ C, f = 1.0mhz)

Symbol	Parameter	Conditions ⁽²⁾	Max.	Unit
Cin	Input Capacitance	VIN = 3dV	9	pF
Соит	Output Capacitance	Vout = 3dV	10	pF
NOTEC				3740 tbl 03

NOTES:

1. This parameter is determined by device characterization but is not production tested.

2. 3dV represents the interpolated capacitance when the input and output signals switch from 0V to 3V or from 3V to 0V.

Recommended DC Operating Conditions

Symbol	Parameter	Min.	Тур.	Max.	Unit
Vdd	Supply Voltage	3.0	3.3	3.6	V
Vss	Ground	0	0	0	V
VIH	Input High Voltage	2.0		VDD+0.3 ⁽²⁾	V
VIL	Input Low Voltage	-0.3 ⁽¹⁾	-	0.8	V
NOTEO				3	3740 tbl 05

NOTES:

1. VIL \geq -1.5V for pulse width less than 10ns.

2. VTERM must not exceed Vcc + 0.3V.

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Industrial and Commercial Temperature Ranges

3740 tbl 06

3740 tbl 08

Truth Table I – Chip Enable^(1,2)

ĈĒ	ĒΕ	CE1	Mode
	Vı∟	V⊪	Port Selected (TTL Active)
L	<u><</u> 0.2V	<u>></u> Vcc -0.2V	Port Selected (CMOS Active)
	V⊮	Х	Port Deselected (TTL Inactive)
н	Х	VIL	Port Deselected (TTL Inactive)
	<u>></u> Vcc -0.2V	X ⁽³⁾	Port Deselected (CMOS Inactive)
	X ⁽³⁾	<u><</u> 0.2V	Port Deselected (CMOS Inactive)

NOTES:

1. Chip Enable references are shown above with the actual TEo and CE1 levels; TE is a reference only.

2. 'H' = VIH and 'L' = VIL.

3. CMOS standby requires 'X' to be either $\leq 0.2V$ or \geq Vcc-0.2V.

Truth Table II - Non-Contention Read/Write Control

	Inpu	uts ⁽¹⁾		Outputs				
CE ⁽²⁾	R/₩	ŌĒ	SEM	I/O0-7	Mode			
Н	Х	Х	Н	High-Z	Deselected: Power-Down			
L	L	Х	Н	DATAIN	Write to Memory			
L	Н	L	Н	DATAOUT	Read Memory			
Х	Х	Н	Х	High-Z	Outputs Disabled			
NOTEC					3740 tbl 07			

NOTES:

1. AOL — A15L \neq AOR — A15R

2. Refer to Chip Enable Truth Table.

Truth Table III – Semaphore Read/Write Control⁽¹⁾

	Inpu	uts ⁽¹⁾		Outputs				
CE ⁽²⁾	R/W	ŌĒ	SEM	I/O0-7	Mode			
Н	Н	L	L	DATAOUT	Read Semaphore Flag Data Out			
Н	\uparrow	Х	L	DATAIN	Write I/Oo into Semaphore Flag			
L	Х	Х	L		Not Allowed			

NOTES:

1. There are eight semaphore flags written to I/Oo and read from all the I/Os (I/Oo-I/O7). These eight semaphore flags are addressed by Ao-A2.

2. Refer to Chip Enable Truth Table.

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Industrial and Commercial Temperature Ranges

DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range ($V_{DD} = 3.3V \pm 0.3V$)

			70V08S		70V		
Symbol	Parameter	Test Conditions	Min.	Max.	Min.	Max.	Unit
Lu	Input Leakage Current ⁽¹⁾	VDD = 3.6V, VIN = 0V to VDD	_	10	_	5	μA
Ilo	Output Leakage Current	$\overline{C}\overline{E}^{(2)} = V_{IH}$, Vout = 0V to VDD		10		5	μA
Vol	Output Low Voltage	Iol = +4mA	_	0.4	_	0.4	V
Vон	Output High Voltage	IOH = -4mA	2.4		2.4		V

NOTES:

1. At VDD \leq 2.0V, input leakages are undefined.

2. Refer to Chip Enable Truth Table.

DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range^(1,6) ($V_{DD} = 3.3V \pm 0.3V$)

Symbol	Parameter	Test Condition	Versio	on		8X15 Only Max		8X20 & Ind Max	Unit
DD	Dynamic Operating Current (Both Ports Active)	$\overline{\underline{CE}} = V_{\mathbb{H}}, \text{ Outputs Disabled}$ $\overline{SEM} = V_{\mathbb{H}}$	COM'L	S L	170 170	260 225	165 165	255 220	mA
		$f = fMAX^{(3)}$	IND	S L			 165	 280	
ISB1	Standby Current (Both Ports - TTL Level	$\overline{\underline{CE}}_{L} = \overline{\underline{CE}}_{R} = V_{H}$ $\overline{SEM}_{R} = \overline{SEM}_{L} = V_{H}$	COM'L	S L	44 44	70 60	39 39	60 50	mA
	Inputs)	$f = fMAX^{(3)}$	IND	S L			39	65	
ISB2	32 Standby Current (One Port - TTL Level Inputs)	el Inputs) $ \begin{array}{ c c c c c }\hline \overline{C}\overline{E}^*A^* &= V_{IL} \mbox{ and } \overline{C}\overline{E}^*B^* &= V_{IH}^{(5)} \\ Active \mbox{ Port Outputs Disabled,} \\ \frac{f-f_{MAX}^{(3)}}{SEM_R} &= \overline{SEM}_L &= V_{IH} \end{array} $	COM'L	S L	115 115	160 145	105 105	155 140	mA
			IND	S L			 105	 155	
ISB3	Full Standby Current (Both Ports - All CMOS Level	Both Ports $\overline{CE}L$ and $\overline{CE}R \ge VDD - 0.2V$	COM'L	S L	1.0 0.2	6 3	1.0 0.2	6 3	mA
	Inputs)	$ \begin{array}{l} \mbox{Vin} \geq \mbox{Vdd} \ \ \ \ \ \ \ \ \ \ \ \ $	IND	S L			 0.2	6	
ISB4	Full Standby Current (One Port - All CMOS Level Inputs)	$\label{eq:constraints} \begin{array}{ c c c c c } \hline \hline CE^*A^* &\leq 0.2V \text{ and} \\ \hline CE^*B^* &\geq VDD &- 0.2V^{(5)} \\ \hline SEMR &= SEML \geq VDD &- 0.2V \\ \hline VIN \geq VDD &- 0.2V \text{ or } VIN \leq 0.2V \\ \hline Active Port Outputs Disabled \\ f &= f_MAX^{(3)} \end{array}$	COM'L	S L	115 115	155 140	105 105	150 135	mA
			IND	S L			 105	 150	

3740 tbl 10a

3740 tbl 09

NOTES:

1. 'X' in part numbers indicates power rating (S or L)

2. VDD = 3.3V, TA = +25 $^\circ\text{C},$ and are not production tested. IDD $_{\text{DC}}$ = 90mA (Typ.)

3. At f = fMax, address and control lines (except Output Enable) are cycling at the maximum frequency read cycle of 1/tRc, and using "AC Test Conditions" of input levels of GND to 3V.

4. f = 0 means no address or control lines change.

5. Port "A" may be either left or right port. Port "B" is the opposite from port "A".

6. Refer to Chip Enable Truth Table.

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DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range^(1,6) (VDD = $3.3V \pm 0.3V$)

Symbol	Parameter	Test Condition	Versi	on		8X25 Only Max		8X35 I Only Max	Uni
DD	Dynamic Operating Current (Both Ports Active)	$\frac{\overline{CE} = V_{IL}, \text{ Outputs Disabled}}{\overline{SEM} = V_{IH}}$ $f = \int_{Max}^{(3)}$	COM'L	S L	120 120	205 170	110 110	195 160	m/
		1 = IMAX*'	IND	S L					
I SB1	(Both Ports - TTL Level	$\overline{\underline{CE}}_{L} = \overline{\underline{CE}}_{R} = V_{H}$ $\overline{SEM}_{R} = S\overline{\underline{SEM}}_{L} = V_{H}$	COM'L	S L	17 15	45 40	15 13	40 35	m
		$f = fMAX^{(3)}$		S L					
ISB2	sB2 Standby Current (One Port - TTL Level Inputs)	$\label{eq:cellson} \begin{split} \overline{CE}^{*} A^{*} &= V_{IL} \text{ and } \overline{CE}^{*} B^{*} &= V_{IH}^{(5)} \\ \text{Active Port Outputs Disabled,} \\ \overline{f=f_{MA} x^{(3)}} \\ \overline{SEM}_{R} &= \overline{SEM}_{L} &= V_{IH} \end{split}$	COM'L	S L	60 60	115 100	50 50	105 90	m
			IND	S L					
ISB3	Full Standby Current (Both Ports - All CMOS Level	Both Ports \overline{CE} and $\overline{CE}_{R} \ge VDD - 0.2V$	COM'L	S L	1.0 0.2	6 3	1.0 0.2	6 3	m
	Inputs)	$ \begin{array}{l} \mbox{Vin} \geq \mbox{Vdd} \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ $	IND	S L					
ISB4	$ \begin{array}{ c c c c c c } \hline Full Standby Current \\ (One Port - All CMOS Level \\ Inputs) \end{array} & \hline \overline{CE}^{}a^{*} \leq 0.2V \text{ and} \\ \hline \overline{CE}^{}B^{*} \geq VDD - 0.2V \text{ and} \\ \hline \overline{SEMR} = \overline{SEML} \geq VDD - 0.2V \\ VIN \geq VDD - 0.2V \text{ or } VIN \leq 0.2V \\ Active Port Outputs Disabled \\ f = f_{MAX}^{(3)} \end{array} $	$\frac{\overline{CE}"B"}{SEMR} = \frac{VDD}{SEML} + 0.2V^{(5)}$	COM'L	S L	70 70	110 95	60 60	100 85	m
		IND	S L						

NOTES:

1. 'X' in part numbers indicates power rating (S or L)

2. VDD = 3.3V, TA = +25 $^\circ\text{C}$, and are not production tested. IDD DC = 90mA (Typ.)

3. At f = fmax, address and control lines (except Output Enable) are cycling at the maximum frequency read cycle of 1/trc, and using "AC Test Conditions" of input levels of GND to 3V.

4. f = 0 means no address or control lines change.

5. Port "A" may be either left or right port. Port "B" is the opposite from port "A".

6. Refer to Chip Enable Truth Table.

AC Test Conditions

Input Pulse Levels	GND to 3.0V	ļ	
Input Rise/Fall Times	3ns Max.	\lesssim 590 Ω	\lesssim 590 Ω
Input Timing Reference Levels	1.5V		
Output Reference Levels	1.5V	ÎNT <	
Output Load	Figures 1 and 2	$435\Omega \leq - 30pF$	$435\Omega \leq = 5pF$
	3740 tbl 11	- -	• •



3.3V

3740 drw 03

Figure 2. Output Test Load (for tLz, tHz, twz, tow) * Including scope and jig.

3.3V

3740 drw 04

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Industrial and Commercial Temperature Ranges

AC Electrical Characteristics Over the

Operating Temperature and Supply Voltage Range⁽⁴⁾

			70V08X15 Com'l Only		70V08X20 Com'l & Ind	
Symbol	Parameter	Min.	Max.	Min.	Max.	Unit
READ CYCLE		-				<u></u>
trc	Read Cycle Time	15		20		ns
taa	Address Access Time		15		20	ns
tace	Chip Enable Access Time ⁽³⁾	_	15		20	ns
taoe	Output Enable Access Time		10		12	ns
toн	Output Hold from Address Change	3		3		ns
tLZ	Output Low-Z Time ^(1,2)	3		3		ns
tHZ	Output High-Z Time ^(1,2)		12		12	ns
tPU	Chip Enable to Power Up Time ^(2,5)	0		0		ns
tpd	Chip Disable to Power Down Time ^(2,5)		15		20	ns
tsop	Semaphore Flag Update Pulse (OE or SEM)	10		10		ns
tsaa	Semaphore Address Access Time	_	15		20	ns

3740 tbl 12a

			18X25 I Only)8X35 I Only	
Symbol	Parameter	Min.	Max.	Min.	Max.	Unit
READ CYCLE	•					
trc	Read Cycle Time	25		35		ns
taa	Address Access Time		25		35	ns
tace	Chip Enable Access Time ⁽³⁾		25		35	ns
taoe	Output Enable Access Time		15		20	ns
tон	Output Hold from Address Change	3	_	3		ns
t∟z	Output Low-Z Time ^(1,2)	3	_	3		ns
tHZ	Output High-Z Time ^(1,2)	_	15		20	ns
tPU	Chip Enable to Power Up Time ^(2,5)	0		0		ns
t PD	Chip Disable to Power Down Time ^(2,5)		25		45	ns
tsop	Semaphore Flag Update Pulse (OE or SEM)	15		15		ns
tsaa	Semaphore Address Access Time		35		45	ns

3740 tbl 12b

NOTES:

1. Transition is measured 0mV from Low or High-impedance voltage with Output Test Load (Figure 2).

2. This parameter is guaranteed by device characterization, but is not production tested. 3. To access RAM, $\overline{CE} = V_{IL}$ and $\overline{SEM} = V_{IL}$. To access semaphore, $\overline{CE} = V_{IH}$ and $\overline{SEM} = V_{IL}$.

4. 'X' in part numbers indicates power rating (S or L).

5. Refer to Chip Enable Truth Table.

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Industrial and Commercial Temperature Ranges

Waveform of Read Cycles⁽⁵⁾



NOTES:

- 1. Timing depends on which signal is asserted last, \overline{OE} or \overline{CE} .
- 2. Timing depends on which signal is de-asserted first \overline{CE} or \overline{OE} .
- 3. tbdd delay is required only in cases where the opposite port is completing a write operation to the same address location. For simultaneous read operations BUSY has no relation to valid output data.
- 4. Start of valid data depends on which timing becomes effective last tAOE, tACE, tAA or tBDD.
- 5. $\overline{SEM} = VIH.$
- 6. Refer to Chip Enable Truth Table.

Timing of Power-Up Power-Down



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Industrial and Commercial Temperature Ranges

AC Electrical Characteristics Over the Operating Temperature and Supply Voltage⁽⁵⁾

			08X15 I Only	Co)8X20 om'l Ind	
Symbol	Parameter	Min.	Мах.	Min.	Max.	Unit
WRITE CY	CLE					
twc	Write Cycle Time	15		20		ns
tew	Chip Enable to End-of-Write ⁽³⁾	12	_	15		ns
taw	Address Valid to End-of-Write	12		15		ns
tas	Address Set-up Time ⁽³⁾	0	_	0	_	ns
twp	Write Pulse Width	12	_	15	_	ns
twr	Write Recovery Time	0	_	0	_	ns
tow	Data Valid to End-of-Write	10	_	15	_	ns
tHZ	Output High-Z Time ^(1,2)	_	10	—	10	ns
tDH	Data Hold Time ⁽⁴⁾	0	_	0	_	ns
twz	Write Enable to Output in High-Z ^(1,2)	—	10	—	10	ns
tow	Output Active from End-of-Write ^(1,2,4)	0	_	0	_	ns
tswrd	SEM Flag Write to Read Time	5	_	5	_	ns
tsps	SEM Flag Contention Window	5	_	5	_	ns
						3740 tbl 13
		70V0 Com')8X25 I Only	70V0 Com'	08X35 IOnly	
Symbol	Parameter	Min.	Мах.	Min.	Max.	Unit
WRITE CY	CLE					
twc	Write Cycle Time	25		35		ns
tew	Chip Enable to End-of-Write ⁽³⁾	20		30		ns
taw	Address Valid to End-of-Write	20	_	30		ns
tas	Address Set-up Time ⁽³⁾	0		0		ns
twp	Write Pulse Width	20		25		ns
twr	Write Recovery Time	0		0		ns
tow	Data Valid to End-of-Write	15		20		ns
tнz	Output High-Z Time ^(1,2)	_	15		20	ns
	· · ·	I		ļ		

0

0

5

5

ns

ns

ns

ns

ns 3740 tbl 13b

20

0

0

5

5

15

This parameter is guaranteed by device characterization, but is not production tested.
 To access RAM, CE = VIL and SEM = VIH. To access semaphore, CE = VIH and SEM = VIL. Either condition must be valid for the entire tew time.

1. Transition is measured 0mV from Low or High-impedance voltage with Output Test Load (Figure 2).

4. The specification for tDH must be met by the device supplying write data to the RAM under all operating conditions. Although tDH and tow values will vary over voltage and temperature, the actual tDH will always be smaller than the actual tow.

5. 'X' in part numbers indicates power rating (S or L).

Data Hold Time⁽⁴⁾

Write Enable to Output in High-Z^(1,2)

Output Active from End-of-Write^(1,2,4)

SEM Flag Write to Read Time

SEM Flag Contention Window

tDн

twz

tow

tswrd

tsps

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Industrial and Commercial Temperature Ranges

Timing Waveform of Write Cycle No. 1, R/W Controlled Timing^(1,5,8)



Timing Waveform of Write Cycle No. 2, **CE** Controlled Timing^(1,5)



- 1. R/\overline{W} or \overline{CE} must be HIGH during all address transitions.
- 2. A write occurs during the overlap (tew or twp) of a LOW CE and a LOW R/W for memory array writing cycle.
- 3. two is measured from the earlier of CE or R/W (or SEM or R/W) going HIGH to the end of write cycle.
- 4. During this period, the I/O pins are in the output state and input signals must not be applied.
- 5. If the CE or SEM LOW transition occurs simultaneously with or after the RW LOW transition, the outputs remain in the High-impedance state.
- 6. Timing depends on which enable signal is asserted last, \overline{CE} or R/\overline{W} .
- 7. This parameter is guaranteed by device characterization, but is not production tested. Transition is measured 0mV from steady state with the Output Test Load (Figure 2).
- If OE is LOW during RW controlled write cycle, the write pulse width must be the larger of twp or (twz + tow) to allow the I/O drivers to turn off and data to be placed on the bus for the required tow. If OE is HIGH during an R/W controlled write cycle, this requirement does not apply and the write pulse can be as short as the specified twp.
- 9. To access RAM, CE = VIL and SEM = VIH. To access semaphore, CE = VIH and SEM = VIL. tew must be met for either condition.
- 10. Refer to Chip Enable Truth Table.

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Industrial and Commercial Temperature Ranges

Timing Waveform of Semaphore Read after Write Timing, Either Side⁽¹⁾



NOTES:

1. CE = VIH for the duration of the above timing (both write and read cycle) (Refer to Chip Enable Truth Table).

2. DATAOUT VALID represents I/Oo-7 equal to semaphore value.

Timing Waveform of Semaphore Write Contention^(1,3,4)



- 1. DOR = DOL = VIL, $\overline{CE}L = \overline{CE}R = VIH$ (Refer to Chip Enable Truth Table).
- All timing is the same for left and right ports. Port "A" may be either left or right port. "B" is the opposite from port "A".
 This parameter is measured from R/W⁻a" or SEM^{*}A" going HIGH to R/W⁻B" or SEM^{*}B" going HIGH.
- 4. If tsps is not satisfied, there is no guarantee which side will be granted the semaphore flag.

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Industrial and Commercial Temperature Ranges

3740 tbl 14b

AC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range⁽⁶⁾

			8X15 I Only	Co)8X20 m'l Ind	
Symbol	Parameter	Min.	Max.	Min.	Max.	Unit
BUSY TIM	IING (M/S=Vih)		-		-	
t BAA	BUSY Access Time from Address Match		15		20	ns
tBDA	BUSY Disable Time from Address Not Matched		15		20	ns
t BAC	BUSY Access Time from Chip Enable Low		15		20	ns
tbdc	BUSY Access Time from Chip Enable High		15		20	ns
taps	Arbitration Priority Set-up Time ⁽²⁾	5		5		ns
tBDD	BUSY Disable to Valid Data ⁽³⁾		17		35	ns
twн	Write Hold After BUSY ⁽⁵⁾	12		15		ns
BUSY TIM	IING (M/S=VIL)					
twв	BUSY Input to Write ⁽⁴⁾	0		0		ns
twн	Write Hold After BUSY ⁶⁾	12		15		ns
PORT-TO-	PORT DELAY TIMING	_	-		-	
twdd	Write Pulse to Data Delay ⁽¹⁾	—	30		45	ns
todd	Write Data Valid to Read Data Delay ⁽¹⁾		25		30	ns
					37	40 tbl 14a
		T				
			8X25 I Only		08X35 I Only	
Symbol	Parameter)8X35	Unit
-	Parameter IING (M/ S =VIH)	Com'	l Only	Com'	8X35 I Only	
-		Com'	l Only	Com'	8X35 I Only	
BUSY TIM	I IING (M/Š=Vih)	Com'	l Only Max.	Com' Min.	08X35 I Only Max.	Unit
BUSY TIM	BUSY Access Time from Address Match	Com' Min.	I Only Max. 25	Com' Min.	08X35 I Only Max. 35	Unit
BUSY TIM tBAA tBDA	ING (M/S=VIH) BUSY Access Time from Address Match BUSY Disable Time from Address Not Matched	Com' Min.	Only Max. 25 25	Com' Min. 	08X35 I Only Max. 35 35	Unit ns ns
BUSY TIM tBAA tBDA tBAC	ING (M/S=VIH) BUSY Access Time from Address Match BUSY Disable Time from Address Not Matched BUSY Access Time from Chip Enable Low	Com' Min.	Only Max. 25 25 25 25	Com' Min. 	8X35 I Only Max. 35 35 35	Unit ns ns ns
BUSY TIM tBAA tBDA tBAC tBDC	ING (M/S=VIH) BUSY Access Time from Address Match BUSY Disable Time from Address Not Matched BUSY Access Time from Chip Enable Low BUSY Access Time from Chip Enable High	Com' Min. — — —	Only Max. 25 25 25 25	Com' Min. 	8X35 I Only Max. 35 35 35	Unit ns ns ns
BUSY TIM tBAA tBDA tBAC tBDC tAPS	ING (M/S=VIH) BUSY Access Time from Address Match BUSY Disable Time from Address Not Matched BUSY Access Time from Chip Enable Low BUSY Access Time from Chip Enable High Arbitration Priority Set-up Time ⁽²⁾	Com' Min. — — —	Only Max. 25 25 25 25 25 25 25 25 25 25 25	Com' Min. 	8X35 Only Max. 35 35 35 35 35 	Unit NS NS NS NS NS
BUSY TIM tBAA tBDA tBDC tBDC tAPS tBDD tWH	BUSY Access Time from Address Match BUSY Disable Time from Address Not Matched BUSY Access Time from Chip Enable Low BUSY Access Time from Chip Enable High Arbitration Priority Set-up Time ⁽²⁾ BUSY Disable to Valid Data ⁽³⁾	Com' Min. — — — 5 —	Only Max. 25 25 25 25 25 25 25 25 25 25 25	Com' Min. 	8X35 Only Max. 35 35 35 35 35 	Unit Unit ns ns ns ns ns ns
BUSY TIM tBAA tBDA tBDC tBDC tAPS tBDD tWH	ING (M/S=VIH) BUSY Access Time from Address Match BUSY Disable Time from Address Not Matched BUSY Access Time from Chip Enable Low BUSY Access Time from Chip Enable High Arbitration Priority Set-up Time ⁽²⁾ BUSY Disable to Valid Data ⁽³⁾ Write Hold After BUSY ⁽⁶⁾	Com' Min. — — — 5 —	Only Max. 25 25 25 25 25 25 25 25 25 25 25	Com' Min. 	8X35 Only Max. 35 35 35 35 35 	Unit Unit ns ns ns ns ns ns
BUSY TIM tBAA tBDA tBAC tBAC tBDC tAPS tBDD tWH BUSY TIM	BUSY Access Time from Address Match BUSY Disable Time from Address Not Matched BUSY Access Time from Chip Enable Low BUSY Access Time from Chip Enable High Arbitration Priority Set-up Time ⁽²⁾ BUSY Disable to Valid Data ⁽³⁾ Write Hold After BUSY ⁽⁶⁾	Com' Min. — — 5 — 20	Only Max. 25 25 25 25 25 25 25 25 25 25 25	Com' Min. — — 5 — 25	8X35 Only Max. 35 35 35 35 35 	Unit NS NS NS NS NS NS NS
BUSY TIM tBAA tBDA tBAC tBDC tAPS tBDD tWH BUSY TIM tWB tWH	BUSY Access Time from Address Match BUSY Disable Time from Address Not Matched BUSY Access Time from Chip Enable Low BUSY Access Time from Chip Enable High Arbitration Priority Set-up Time ⁽²⁾ BUSY Disable to Valid Data ⁽³⁾ Write Hold After BUSY ⁽⁶⁾ BUSY Input to Write ⁽⁴⁾	Com' Min. — — — 5 — 20	Only Max. 25 25 25 25 25 25 25 25 25 25 25	Com' Min. — — 5 — 25 0	8X35 Only Max. 35 35 35 35 35 	Unit Unit Unit Unit NS NS NS NS NS NS NS NS NS NS
BUSY TIM tBAA tBDA tBAC tBAC tBDC tAPS tBDD tWH BUSY TIM tWB tWH	BUSY Access Time from Address Match BUSY Disable Time from Address Not Matched BUSY Access Time from Chip Enable Low BUSY Access Time from Chip Enable High Arbitration Priority Set-up Time ⁽²⁾ BUSY Disable to Valid Data ⁽³⁾ Write Hold After BUSY ⁽⁶⁾ BUSY Input to Write ⁽⁴⁾ Write Hold After BUSY ⁽⁶⁾	Com' Min. — — — 5 — 20	Only Max. 25 25 25 25 25 25 25 25 25 25 25	Com' Min. — — 5 — 25 0	8X35 Only Max. 35 35 35 35 35 	Unit Unit ns ns ns ns ns ns ns ns

NOTES:

1. Port-to-port delay through RAM cells from writing port to reading port, refer to "Timing Waveform of Write with Port-to-Port Read and BUSY (M/S = VI+)".

2. To ensure that the earlier of the two ports wins.

3. tBDD is a calculated parameter and is the greater of 0, twDD - twp (actual), or tDDD - tDw (actual).

4. To ensure that the write cycle is inhibited on port "B" during contention on port "A".

5. To ensure that a write cycle is completed on port "B" after contention on port "A".

6. 'X' in part numbers indicates power rating (S or L).

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Timing Waveform of Write with Port-to-Port Read and **BUSY** $(M/S = VIH)^{(2,4,5)}$



NOTES:

- 1. To ensure that the earlier of the two ports wins. taps is ignored for $M/\overline{S} = VIL$ (SLAVE).
- 2. $\overline{CE}_{L} = \overline{CE}_{R} = VIL$, refer to Chip Enable Truth Table.
- OE = VIL for the reading port.
 If M/S = VIL (slave), BUSY is an input. Then for this example BUSY"A" = VIH and BUSY"B" input is shown above.
- 5. All timing is the same for left and right ports. Port "A" may be either the left or right port. Port "B" is the port opposite from port "A".

Timing Waveform of Write with **BUSY** (M/ \overline{S} = VIL)



- 1. twn must be met for both BUSY input (SLAVE) and output (MASTER).
- 2. BUSY is asserted on port "B" blocking R/W"B", until BUSY"B" goes HIGH.
- 3. All timing is the same for left and right ports. Port "A" may be either the left or right port. Port "B" is the port opposite from port "A".



Waveform of **BUSY** Arbitration Cycle Controlled by Address Match Timing $(M/S = VIH)^{(1)}$



- 1. All timing is the same for left and right ports. Port "A" may be either the left or right port. Port "B" is the port opposite from port "A".
- 2. If taps is not satisfied, the BUSY signal will be asserted on one side or another but there is no guarantee on which side BUSY will be asserted.
- 3. Refer to Chip Enable Truth Table.

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AC Electrical Characteristics Over the

Operating Temperature and Supply Voltage Range⁽¹⁾

			8X15 'I Only	Co)8X20 om'l Ind	
Symbol	Parameter	Min.	Мах.	Min.	Max.	Unit
INTERRUPT	riming					
tas	Address Set-up Time	0	_	0		ns
twr	Write Recovery Time	0	_	0	_	ns
tins	Interrupt Set Time	—	15		20	ns
tinr	Interrupt Reset Time	—	25		20	ns
						3740 tbl 15a

			8X25 'I Only		8X35 I Only	
Symbol	Parameter	Min.	Мах.	Min.	Мах.	Unit
INTERRUPT T	MING					
tas	Address Set-up Time	0	l	0	I	ns
twr	Write Recovery Time	0	I	0		ns
tins	Interrupt Set Time		25		30	ns
tinr	Interrupt Reset Time		30		35	ns

NOTES:

1. 'X' in part numbers indicates power rating (S or L).

3740 tbl 15b

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Waveform of Interrupt Timing^(1,5)



NOTES:

1. All timing is the same for left and right ports. Port "A" may be either the left or right port. Port "B" is the port opposite from port "A".

2. Refer to Interrupt Truth Table.

- 3. Timing depends on which enable signal (\overline{CE} or R/\overline{W}) is asserted last.
- 4. Timing depends on which enable signal $(\overline{CE} \text{ or } R/\overline{W})$ is de-asserted first.

5. Refer to Chip Enable Truth Table.

Truth Tables

Truth Table IV — Interrupt Flag^(1,4,5)

	Left Port									
R/₩L	<u>C</u> EL	OEL	A15L-A0L	ĪNTL	R/WR		OE R	A15R-A0R	ĪNTR	Function
L	L	Х	FFFF	Х	Х	Х	Х	Х	L ⁽²⁾	Set Right INTR Flag
Х	Х	Х	Х	Х	Х	L	L	FFFF	H ⁽³⁾	Reset Right INTR Flag
Х	Х	Х	Х	L ⁽³⁾	L	L	Х	FFFE	Х	Set Left INTL Flag
Х	L	L	FFFE	H ⁽²⁾	Х	Х	Х	Х	Х	Reset Left INTL Flag

NOTES:

1. Assumes $\overline{\text{BUSY}}_{L} = \overline{\text{BUSY}}_{R} = VIH$.

2. If $\overline{\text{BUSY}}_{L} = V_{IL}$, then no change.

3. If $\overline{\text{BUSY}}_{R} = V_{IL}$, then no change.

4. INTL and INTR must be initialized at power-up.

5. Refer to Chip Enable Truth Table.

3740 tbl 16

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Truth Table V — Address **BUSY** Arbitration⁽⁴⁾

	In				
ĒĒ∟	ĊĒr	Aol-A15l Aor-A15r	BUS YL ⁽¹⁾	BUS YR ⁽¹⁾	Function
Х	Х	NO MATCH	Н	Н	Normal
Н	Х	MATCH	Н	Н	Normal
Х	Н	MATCH	Н	Н	Normal
L	L	MATCH	(2)	(2)	Write Inhibit ⁽³⁾

NOTES:

3740 tbl 17

1. Pins BUSYL and BUSYL and BUSYL and BUSYL and BUSY are both outputs when the part is configured as a master. Both are inputs when configured as a slave. BUSY outputs on the IDT70V08 are pushpull, not open drain outputs. On slaves the BUSY input internally inhibits writes.

 "L" if the inputs to the opposite port were stable prior to the address and enable inputs of this port. "H" if the inputs to the opposite port became stable after the address and enable inputs of this port. If tAPS is not met, either BUSYL or BUSYR = LOW will result. BUSYL and BUSYR outputs can not be LOW simultaneously.

3. Writes to the left port are internally ignored when BUSYL outputs are driving LOW regardless of actual logic level on the pin. Writes to the right port are internally ignored when BUSYR outputs are driving LOW regardless of actual logic level on the pin.

4. Refer to Chip Enable Truth Table.

Truth Table VI — Example of Semaphore Procurement Sequence^(1,2,3)

Functions	Do - D7 Left	Do - D7 Right	Status
No Action	1	1	Semaphore free
Left Port Writes "0" to Semaphore	0	1	Left port has semaphore token
Right Port Writes "0" to Semaphore	0	1	No change. Right side has no write access to semaphore
Left Port Writes "1" to Semaphore	1	0	Right port obtains semaphore token
Left Port Writes "0" to Semaphore	1	0	No change. Left port has no write access to semaphore
Right Port Writes "1" to Semaphore	0	1	Left port obtains semaphore token
Left Port Writes "1" to Semaphore	1	1	Semaphore free
Right Port Writes "0" to Semaphore	1	0	Right port has semaphore token
Right Port Writes "1" to Semaphore	1	1	Semaphore free
Left Port Writes "0" to Semaphore	0	1	Left port has semaphore token
Left Port Writes "1" to Semaphore	1	1	Semaphore free

NOTES:

1. This table denotes a sequence of events for only one of the eight semaphores on the IDT70V08.

2. There are eight semaphore flags written to via I/Oo and read from all I/O's (I/Oo-I/O7). These eight semaphores are addressed by Ao - A2.

3. TE = VIH, SEM = VIL to access the semaphores. Refer to the Semaphore Read/Write Control Truth Table.

Functional Description

The IDT70V08 provides two ports with separate control, address and I/O pins that permit independent access for reads or writes to any location in memory. The IDT70V08 has an automatic power down feature controlled by \overline{CE} . The $\overline{CE}o$ and CE1 control the on-chip power down circuitry that permits the respective port to go into a standby mode when not selected (\overline{CE} HIGH). When a port is enabled, access to the entire memory array is permitted.

box or message center) is assigned to each port. The left port interrupt flag (\overline{INTL}) is asserted when the right port writes to memory location FFFE (HEX), where a write is defined as $\overline{CER} = R/\overline{WR} = VIL$ per the Truth Table. The left port clears the interrupt through access of address location FFFE when $\overline{CEL} = \overline{OEL} = VIL$, R/\overline{W} is a "don't care". Likewise, the right port interrupt flag (\overline{INTR}) is asserted when the left port writes to memory location FFFF (HEX) and to clear the interrupt flag (INTR), the right port must read the memory location FFFF. The message (8 bits) at FFFE or FFFF is user-defined since it is an addressable SRAM location. If the interrupt function is not used,

3740 tbl 18

Interrupts

If the user chooses the interrupt function, a memory location (mail

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address locations FFFE and FFFF are not used as mail boxes, but as part of the random access memory. Refer to Truth Table IV for the interrupt operation.

Busy Logic

Busy Logic provides a hardware indication that both ports of the RAM have accessed the same location at the same time. It also allows one of the two accesses to proceed and signals the other side that the RAM is "Busy". The BUSY pin can then be used to stall the access until the operation on the other side is completed. If a write operation has been attempted from the side that receives a BUSY indication, the write signal is gated internally to prevent the write from proceeding.

The use of $\overline{\text{BUSY}}$ logic is not required or desirable for all applications. In some cases it may be useful to logically OR the $\overline{\text{BUSY}}$ outputs together and use any $\overline{\text{BUSY}}$ indication as an interrupt source to flag the event of an illegal or illogical operation. If the write inhibit function of $\overline{\text{BUSY}}$ logic is not desirable, the $\overline{\text{BUSY}}$ logic can be disabled by placing the part in slave mode with the M/S pin. Once in slave mode the $\overline{\text{BUSY}}$ pin operates solely as a write inhibit input pin. Normal operation can be programmed by tying the $\overline{\overline{\text{BUSY}}}$ pins HIGH. If desired, unintended write operations can be prevented to a port by tying the $\overline{\overline{\text{BUSY}}}$ pin for



Figure 3. Busy and chip enable routing for both width and depth expansion with IDT70V08 RAMs.

that port LOW.

The BUSY outputs on the IDT 70V08 RAM in master mode, are push-pull type outputs and do not require pull up resistors to operate. If these RAMs are being expanded in depth, then the BUSY indication for the resulting array requires the use of an external AND gate.

Width Expansion with Busy Logic Master/Slave Arrays

When expanding an IDT70V08 RAM array in width while using BUSY logic, one master part is used to decide which side of the RAMs array will receive a BUSY indication, and to output that indication. Any number of slaves to be addressed in the same address range as the master use the BUSY signal as a write inhibit signal. Thus on the IDT70V08 RAM the BUSY pin is an output if the part is used as a master (M/S pin = VIH), and the BUSY pin is an input if the part used as a slave (M/S pin = VIL) as shown in Figure 3.

If two or more master parts were used when expanding in width, a split decision could result with one master indicating BUSY on one side

of the array and another master indicating **BUSY** on one other side of the array. This would inhibit the write operations from one port for part of a word and inhibit the write operations from the other port for the other part of the word.

The BUSY arbitration on a master is based on the chip enable and address signals only. It ignores whether an access is a read or write. In a master/slave array, both address and chip enable must be valid long enough for a BUSY flag to be output from the master before the actual write pulse can be initiated with the R/W signal. Failure to observe this timing can result in a glitched internal write inhibit signal and corrupted data in the slave.

Semaphores

The IDT70V08 is an extremely fast Dual-Port 64K x 8 CMOS Static RAM with an additional 8 address locations dedicated to binary semaphore flags. These flags allow either processor on the left or right side of the Dual-Port RAM to claim a privilege over the other processor for functions defined by the system designer's software. As an example, the semaphore can be used by one processor to inhibit the other from accessing a portion of the Dual-Port RAM or any other shared resource.

The Dual-Port RAM features a fast access time, with both ports being completely independent of each other. This means that the activity on the left port in no way slows the access time of the right port. Both ports are identical in function to standard CMOS Static RAM and can be read from or written to at the same time with the only possible conflict arising from the simultaneous writing of, or a simultaneous READ/WRITE of, a non-semaphore location. Semaphores are protected against such ambiguous situations and may be used by the system program to avoid any conflicts in the non-semaphore portion of the Dual-Port RAM. These devices have an automatic power-down feature controlled by \overline{CE} , the Dual-Port RAM enable, and \overline{SEM} , the semaphore enable. The \overline{CE} and \overline{SEM} pins control on-chip power down circuitry that permits the respective port to go into standby mode when not selected. This is the condition which is shown in Truth Table III where \overline{CE} and \overline{SEM} are both HIGH.

Systems which can best use the IDT70V08 contain multiple processors or controllers and are typically very high-speed systems which are software controlled or software intensive. These systems can benefit from a performance increase offered by the IDT70V08s hardware semaphores, which provide a lockout mechanism without requiring complex programming.

Software handshaking between processors offers the maximum in system flexibility by permitting shared resources to be allocated in varying configurations. The IDT70V08 does not use its semaphore flags to control any resources through hardware, thus allowing the system designer total flexibility in system architecture.

An advantage of using semaphores rather than the more common methods of hardware arbitration is that wait states are never incurred in either processor. This can prove to be a major advantage in very high-speed systems.

How the Semaphore Flags Work

The semaphore logic is a set of eight latches which are independent of the Dual-Port RAM. These latches can be used to pass a flag, or token, from one port to the other to indicate that a shared resource

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is in use. The semaphores provide a hardware assist for a use assignment method called "Token Passing Allocation." In this method, the state of a semaphore latch is used as a token indicating that a shared resource is in use. If the left processor wants to use this resource, it requests the token by setting the latch. This processor then verifies its success in setting the latch by reading it. If it was successful, it proceeds to assume control over the shared resource. If it was not successful in setting the latch, it determines that the right side processor has set the latch first, has the token and is using the shared resource. The left processor can then either repeatedly request that semaphore's status or remove its request for that semaphore to perform another task and occasionally attempt again to gain control of the token via the set and test sequence. Once the right side has relinquished the token, the left side should succeed in gaining control.

The semaphore flags are active LOW. A token is requested by writing a zero into a semaphore latch and is released when the same side writes a one to that latch.

The eight semaphore flags reside within the IDT70V08 in a separate memory space from the Dual-Port RAM. This address space is accessed by placing a low input on the \overline{SEM} pin (which acts as a chip select for the semaphore flags) and using the other control pins (Address, \overline{CE} , and R/\overline{W}) as they would be used in accessing a standard Static RAM. Each of the flags has a unique address which can be accessed by either side through address pins A0 – A2. When accessing the semaphores, none of the other address pins has any effect.

When writing to a semaphore, only data pin Do is used. If a low level is written into an unused semaphore location, that flag will be set to a zero on that side and a one on the other side (see Truth Table VI). That semaphore can now only be modified by the side showing the zero. When a one is written into the same location from the same side, the flag will be set to a one for both sides (unless a semaphore request from the other side is pending) and then can be written to by both sides. The fact that the side which is able to write a zero into a semaphore subsequently locks out writes from the other side is what makes semaphore flags useful in interprocessor communications. (A thorough discussion on the use of this feature follows shortly.) A zero written into the same location from the other side will be stored in the semaphore request latch for that side until the semaphore is freed by the first side.

When a semaphore flag is read, its value is spread into all data bits so that a flag that is a one reads as a one in all data bits and a flag containing a zero reads as all zeros. The read value is latched into one side's output register when that side's semaphore select (SEM) and output enable (\overline{OE}) signals go active. This serves to disallow the semaphore from changing state in the middle of a read cycle due to a write cycle from the other side. Because of this latch, a repeated read of a semaphore in a test loop must cause either signal (SEM or \overline{OE}) to go inactive or the output will never change.

A sequence WRITE/READ must be used by the semaphore in order to guarantee that no system level contention will occur. A processor requests access to shared resources by attempting to write a zero into a semaphore location. If the semaphore is already in use, the semaphore request latch will contain a zero, yet the semaphore flag will appear as one, a fact which the processor will verify by the subsequent read (see Table VI). As an example, assume a processor writes a zero to the left port at a free semaphore location. On a subsequent

Industrial and Commercial Temperature Ranges

read, the processor will verify that it has written successfully to that location and will assume control over the resource in question. Meanwhile, if a processor on the right side attempts to write a zero to the same semaphore flag it will fail, as will be verified by the fact that a one will be read from that semaphore on the right side during subsequent read. Had a sequence of READ/WRITE been used instead, system contention problems could have occurred during the gap between the read and write cycles.

It is important to note that a failed semaphore request must be followed by either repeated reads or by writing a one into the same location. The reason for this is easily understood by looking at the simple logic diagram of the semaphore flag in Figure 4. Two semaphore request latches feed into a semaphore flag. Whichever latch is first to present a zero to the semaphore flag will force its side of the semaphore flag LOW and the other



side HIGH. This condition will continue until a one is written to the same semaphore request latch. Should the other side's semaphore request latch have been written to a zero in the meantime, the semaphore flag will flip over to the other side as soon as a one is written into the first side's request latch. The second side's flag will now stay LOW until its semaphore request latch is written to a one. From this it is easy to understand that, if a semaphore is requested and the processor which requested it no longer needs the resource, the entire system can hang up until a one is written into that semaphore request latch.

The critical case of semaphore timing is when both sides request a single token by attempting to write a zero into it at the same time. The semaphore logic is specially designed to resolve this problem. If simultaneous requests are made, the logic guarantees that only one side receives the token. If one side is earlier than the other in making the request, the first side to make the request will receive the token. If both requests arrive at the same time, the assignment will be arbitrarily made to one port or the other.

One caution that should be noted when using semaphores is that semaphores alone do not guarantee that access to a resource is secure. As with any powerful programming technique, if semaphores are misused or misinterpreted, a software error can easily happen.

Initialization of the semaphores is not automatic and must be handled via the initialization program at power-up. Since any semaphore request flag which contains a zero must be reset to a one, all semaphores on both sides should have a one written into them at initialization from both sides to assure that they will be free when needed.

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Ordering Information



NOTE:

1. Industrial temperature range is available. For other speeds, packages and powers contact your sales office.

 Green parts available. For specific speeds, packages and powers contact your local sales office. LEAD FINISH (SnPb) parts are Obsolete. Product Discontinuation Notice - PDN# SP-17-02 Note that information regarding recently obsoleted parts is included in this datasheet for customer convenience.

Orderable Part Information

Speed (ns)	Orderable Part ID	Pkg. Code	Pkg. Type	Temp. Grade
15	70V08L15PFG	PNG100	TQFP	С
	70V08L15PFG8	PNG100	TQFP	С
20	70V08L20PFGI	PNG100	TQFP	I
	70V08L20PFGI8	PNG100	TQFP	I

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High-Speed 3.3V 64K x 8 Dual-Port Static RAM
High-Speed 3.3V 64K X & Dual-Port Static RAW

	t Document History
3/15/99:	Initiated datasheet document history
	Converted to new format
	Cosmetic and typographical corrections
	Page 2 Added additional notes to pin configurations
	Added 15ns speed grade
06/09/99:	Changed drawing format
11/10/99:	Replaced IDT logo
01/12/01:	Page 3 Increased storage temperature parameter Clarified TA parameter
	Page 5 DC Electric parameters-changed wording from open to disabled
	Page 18 Added IV to Truth Table in first paragraph
	Changed ±200mV to 0mV in notes
	Removed Preliminary status
12/03/01:	Page 2 Added date revision to pin configurations
	Page 2, 3, 5 & 6 Changed naming conventions from Vcc to VDD and from GND to Vss
	Page 5 Added industrial temp for 20ns speed to DC Electrical Characteristics
	Page 7, 9, 12 & 15 Added industrial temp to 20ns speed to AC Electrical Characteristics
	Page 20 Added industrial temp to 20ns and added 3.3V specification to ordering information
	Page 1 & 20 Replaced ™ logo with [®] logo
03/24/04:	Page 5 Corrected the Iod 15ns commercial lower power value to 225mA in the DC Electrical Characteristics table
10/29/08:	Page 20 Removed "IDT" from orderable part number
08/06/09:	Page 1 Added green availability to features
	Page 20 Added green indicator to ordering information
02/27/15:	Page 2 Removed IDT in reference to fabrication
	Page 7 Added footnote "5. Refer to Chip Enable Truth Table" to AC Elec Chars Read Cycle Tables
	Page 2&20 The package code changed from PN100-1 to PN100 to match standard package codes
	Page 20 Added T&R indicators to Ordering Information
11/28/17:	Product Discontinuation Notice - PDN# SP-17-02
	Last time buy expires June 15, 2018
05/30/19:	Page 1 Updated Commercial speed grade offering in Features
	Page 2 Changed diagram for the PNG100 pin configuration by rotating package pin labels and pin numbers
	90 degrees counter clockwise to reflect pin 1 orientation and added pin 1 dot at pin 1
	Aligned the top and bottom pin labels in the standard direction
	Added IDT logo to the PNG100 pin configuration and changed the text to be in alignment with new diagram marking specs
	Updated footnote reference for PNG100
	Page 2 & 20 The package code PN100 changed to PNG100 to match standard package code
	Page 20 Updated Commercial speed grade offering in the Ordering Information
	Page 20 Revised LEAD FINISH note to indicate Obsolete
	Added Orderable Part Information